

isc N-Channel Mosfet Transistor

IRF712

• FEATURES

- Low $R_{DS(on)}$
- V_{GS} Rated at $\pm 20V$
- Silicon Gate for Fast Switching Speed
- Rugged
- Low Drive Requirements

• DESCRIPTION

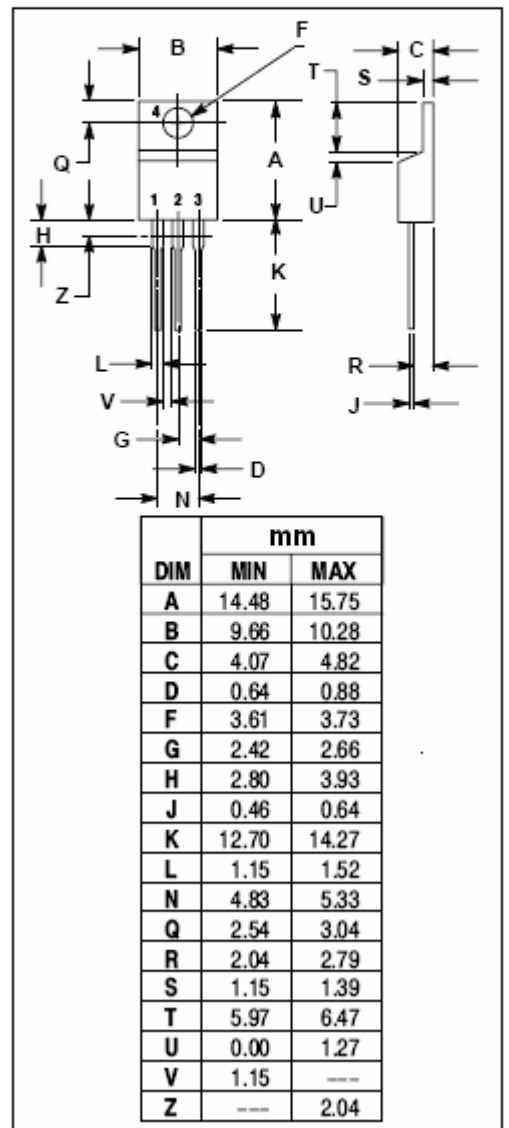
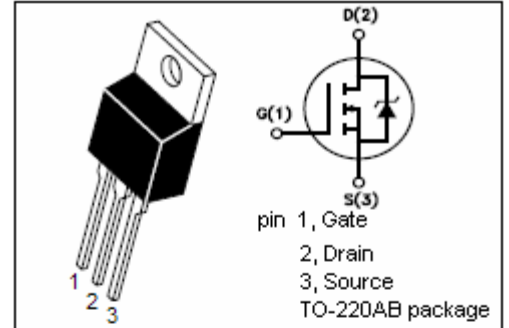
- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	400	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	1.7	A
I_{DM}	Drain Current-Single Plused	4.3	A
P_D	Total Dissipation @ $T_C=25^{\circ}C$	36	W
T_j	Max. Operating Junction Temperature	-55~150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	3.5	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	80	$^{\circ}C/W$



isc N-Channel Mosfet Transistor**IRF712****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=0.25\text{mA}$	400			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25\text{mA}$	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=1.1\text{A}$			5.0	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}= \pm 20\text{V}; V_{DS}=0$			± 500	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=400\text{V}; V_{GS}=0$			250	μA
V_{SD}	Forward On-Voltage	$I_S=2.0\text{A}; V_{GS}=0$			1.6	V
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $F=1.0\text{MHz}$		135		μF
C_{oss}	Output Capacitance			35		μF
C_{rss}	Reverse Transfer Capacitance			8		μF

• SWITCHING CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$T_d(on)$	Turn-on Delay Time	$V_{DD}=50\text{V}, I_D=5.6\text{A}$ $V_{GS}=10\text{V}, R_{GEN}=24\Omega$ $R_{GS}=24\Omega$		8	12	ns
T_r	Rise Time			10	15	ns
$T_d(off)$	Turn-off Delay Time			21	32	ns
T_f	Fall Time			11	17	ns